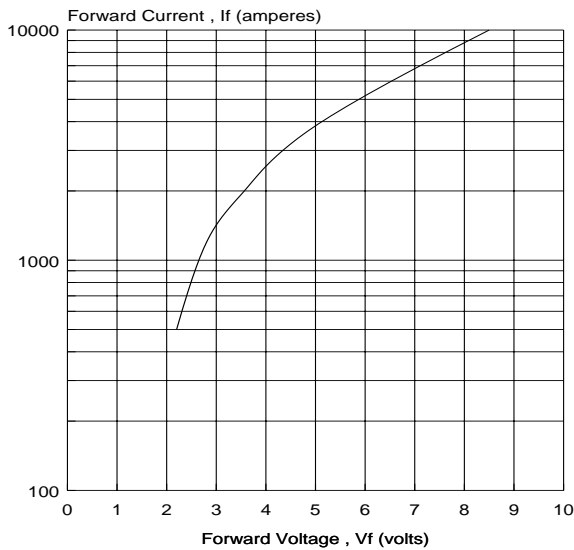
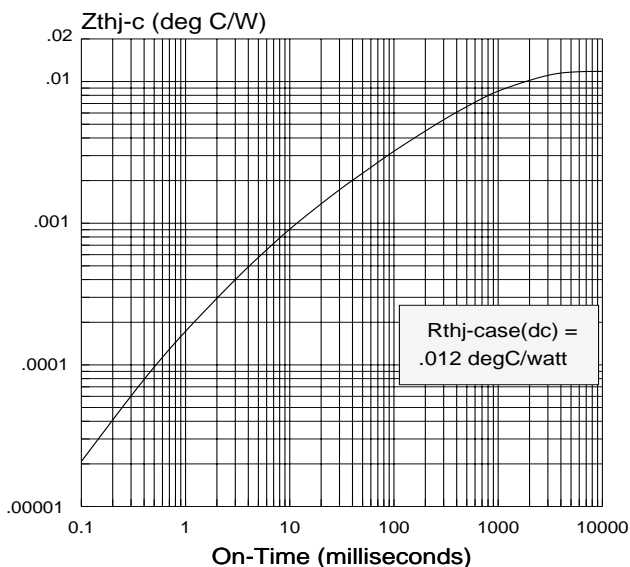


The A881A fast recovery diode is designed as a parallel mate for 1250 Arms GIO's used in voltage fed inverter circuits normally requiring the bypass function. Its relatively low recovery current and charge in combination with low thermal resistance offer a new advantage for optimizing other circuit components. It is manufactured by the proven multi-diffusion process with 77mm diameter silicon and is supplied in a disc-type package ready to mount using commercially available heat dissipators and clamping hardware.

FORWARD CHARACTERISTIC  
Process Maximum @ Tj=125 C



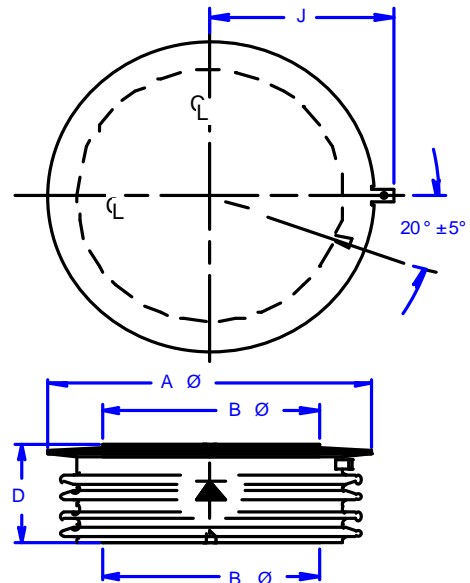
THERMAL IMPEDANCE vs. ON-TIME



**MAXIMUM RATINGS & PARAMETERS**

Maximum repetitive peak reverse voltage	$V_{RRM}$	$T_j = -40$ to $+125^\circ\text{C}$	to 4500	V
Maximum forward average & RMS current ratings	$I_{F(AV)}$ $I_{RMS}$	$T_{case} 70^\circ\text{C}$	800 1250	A
Maximum reverse leakage current	$I_{RRM}$		200	ma
Forward voltage drop	$V_{FM}$	$I_T=2500A$ $t_p=8.3ms$ $T_j=125^\circ\text{C}$	3.75	V
Maximum peak recovery current*	$I_{RR}$	@ 100 A/us @ 400 A/us	350 1000	A
Maximum recovery charge *	$Q_{RR}$	@ 100 A/us @400A/us	1000 2000	$\mu\text{C}$

\*( tested with 5uF GIO snubber)



$A\phi = 4.35$  in (110.5 mm)  
 $B\phi = 2.88$  in (73.2 mm)  
 $D = 1.07$  in (27.2 mm)

**CLAMPING FORCE REQUIRED**  
7000 - 9000 lb / 31.1 - 40.0 kN